

Vishay Siliconix

N-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)		
200	0.080 at V _{GS} = 10 V	4.0		
	0.090 at V _{GS} = 6.0 V	3.8		

FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC

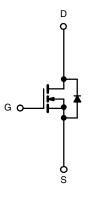


FREE Available

SO-8 S D 8 S D 2 S D 6 3 G D 5 4 Top View

Si4490DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

Ordering Information: Si4490DY-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted Parameter Symbol 10 s **Steady State** Unit **Drain-Source Voltage** V_{DS} 200 ٧ Gate-Source Voltage V_{GS} ± 20 $T_A = 25 \degree C$ 4.0 2.85 Continuous Drain Current (T_J = 150 °C)^a I_D $T_A = 70 \ ^{\circ}C$ 3.2 2.3 Pulsed Drain Current I_{DM} 40 А Avalanch Current L = 0.1 mH 15 I_{AS} I_S 2.6 1.3 Continuous Source Current (Diode Conduction)^a T_A = 25 °C 1.56 3.1 P_D W Maximum Power Dissipation^a T_A = 70 °C 2.0 1.0 Operating Junction and Storage Temperature Range T_J, T_{stg} - 55 to 150 °C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marine lucation to Ambienta	t ≤ 10 s	- R _{thJA}	33	40	
Maximum Junction-to-Ambient ^a	Steady State		65	80	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	17	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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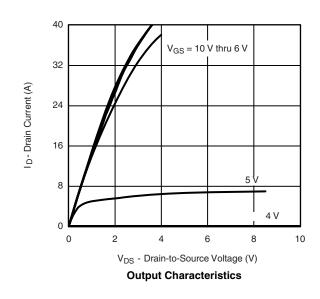


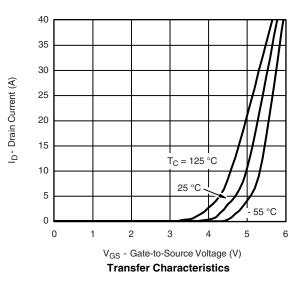
Parameter	Symbol	Test Conditions		Тур.	Max.	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$ 2.0				V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 160 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	μA
		V_{DS} = 160 V, V_{GS} = 0 V, T_{J} = 55 °C			5	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	40			А
	P	V _{GS} = 10 V, I _D = 4.0 A		0.065	0.080	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 6.0 \text{ V}, \text{ I}_{D} = 4.0 \text{ A}$		0.070	0.090	Ω
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 5 \text{ A}$		19		S
Diode Forward Voltage ^a	V _{SD}	$I_{\rm S} = 2.8$ A, $V_{\rm GS} = 0$ V		0.75	1.2	V
Dynamic ^b			•			
Total Gate Charge	Qg			34	42	nC
Gate-Source Charge	Q _{gs}	V_{DS} = 100 V, V_{GS} = 10 V, I_{D} = 4.0 A		7.5		
Gate-Drain Charge	Q _{gd}			12.0		
Gate Resistance	Rg		0.2	0.85	1.3	Ω
Turn-On Delay Time	t _{d(on)}			14	20	
Rise Time	t _r	V_{DD} = 100 V, R_L = 25 Ω		20	30	
Turn-Off Delay Time	t _{d(off)}	$\rm I_D \cong 4.0$ A, $\rm V_{GEN}$ = 10 V, $\rm R_g$ = 6 Ω		32	50	ns
Fall Time	t _f			25	35	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.8 A, dI/dt = 100 A/μs		70	100	

Notes: a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



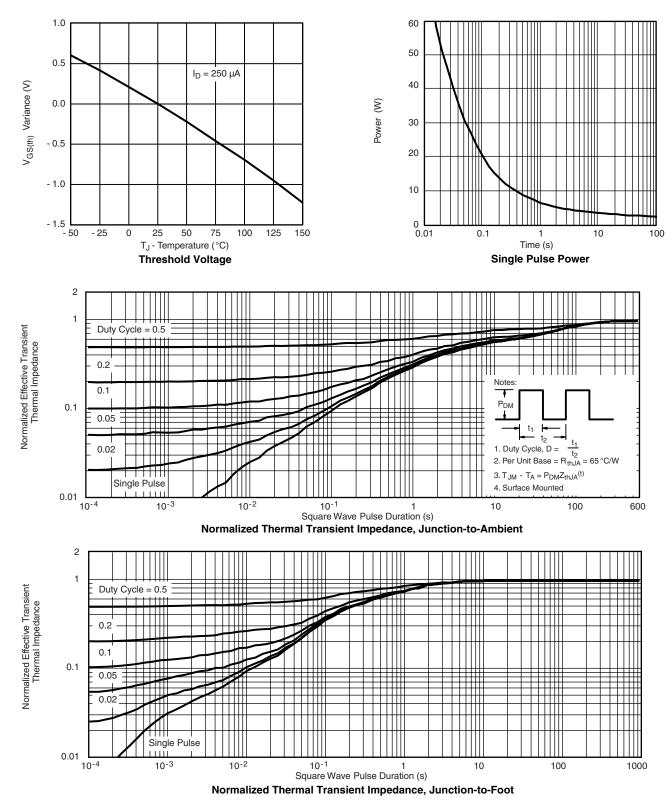


Si4490DY VISHAY Vishay Siliconix TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted 2500 0.20 2000 $R_{DS(on)}$ - On-Resistance (Ω) 0.15 C_{iss} C - Capacitance (pF) 1500 $V_{GS} = 6 V$ 0.10 1000 $V_{GS} = 10 V$ 0.05 500 C_{rss} Coss 0 0.00 0 40 80 120 160 200 8 16 24 40 0 32 V_{DS} - Drain-to-Source Voltage (V) I_D - Drain Current (A) **On-Resistance vs. Drain Current** Capacitance 20 2.5 V_{DS} = 100 V $V_{GS} = 10 V$ I_D = 4.0 A $I_{\rm D} = 4.0 ~\rm{A}$ V_{GS} - Gate-to-Source Voltage (V) 2.0 16 R_{DS(on)} - On-Resistance (Normalized) 12 1.5 1.0 8 4 0.5 0 0.0 0 15 30 45 60 - 50 - 25 0 25 50 75 100 125 150 Q_q - Total Gate Charge (nC) T_J - Junction Temperature (°C) **On-Resistance vs. Junction Temperature Gate Charge** 50 0.25 0.20 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - On-Resistance (Ω) Is - Source Current (A) I_D = 4.0 A T_J = 150 °C 0.15 10 0.10 T_J = 25 °C 0.05 1 0.00 0.0 0.2 0.4 0.6 0.8 1.0 1.2 0 2 4 6 8 10 V_{SD} - Source-to-Drain Voltage (V) V_{GS} - Gate-to-Source Voltage (V) On-Resistance vs. Gate-to-Source Voltage

Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71341.



Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





	MILLIM	IETERS	INCHES			
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27 BSC		0.050 BSC			
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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